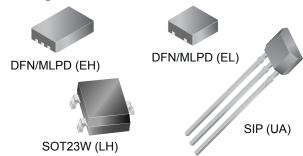


Features and Benefits

- Micropower operation
- Operation with north or south pole
- 2.5 to 3.5 V battery operation
- Chopper stabilized
 - Superior temperature stability
 - Extremely low switchpoint drift
 - Insensitive to physical stress
- High ESD protection
- Solid-state reliability
- Small size
- Easily manufacturable with magnet pole independence

Packages:



Not to scale

Description

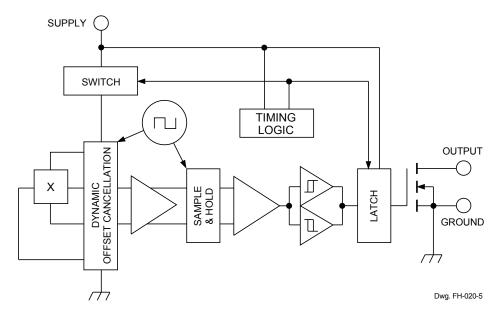
The A 3211 and A3212 integrated circuits are ultrasensitive, pole independent Hall-effect switches with latched digital output. These sensors are especially suited for operation in battery-operated, hand-held equipment such as cellular and cordless telephones, pagers, and palmtop computers. A 2.5 to 3.5 V operation and a unique clocking scheme reduce the average operating power requirements to less than 15 μW with a 2.75 V supply.

Unlike other Hall-effect switches, either a north or south pole of sufficient strength will turn the output on in the A3212, and in the absence of a magnetic field, the output is off. The A3211 provides an inverted output. The polarity independence and minimal power requirements allow these devices to easily replace reed switches for superior reliability and ease of manufacturing, while eliminating the requirement for signal conditioning.

Improved stability is made possible through chopper stabilization (dynamic offset cancellation), which reduces the residual offset voltage normally caused by device overmolding, temperature dependencies, and thermal stress.

Continued on the next page...

Functional Block Diagram



Description (continued)

This device includes on a single silicon chip a Hall-voltage generator, small-signal amplifier, chopper stabilization, a latch, and a MOSFET output. Advanced CMOS processing is used to take advantage of low-voltage and low-power requirements, component matching, very low input-offset errors, and small component geometries.

Four package styles provide magnetically optimized solutions for most applications. Miniature low-profile surface-mount package types EH and EL (0.75 and 0.50 mm nominal height) are leadless, LH is a 3-pin low-profile SMD, and UA is a three-pin SIP for through-hole mounting. Packages are lead (Pb) free (suffix, -T) with 100% matte tin plated leadframes.

Selection Guide

Part Number	Packing ¹	Package	Ambient Temperature T _A (°C)	State in Magnetic Field	
A3211EEHLT-T	3000 pieces per reel	2 mm x 3 mm, 0.75 mm nominal height MLP/DFN			
A3211EELLT-T	3000 pieces per reel	2 mm x 2 mm, 0.50 mm nominal height MLP/DFN	40 40 05	Off	
A3211ELHLT-T	3000 pieces per reel 3-pin surface mount SOT23W		-40 to 85	Oli	
A3211EUA-I ²	500 pieces per bulk bag	SIP-3 through hole			
A3212EEHLT-T	3000 pieces per reel	2 mm x 3 mm, 0.75 mm nominal height MLP/DFN			
A3212EELLT-T	3000 pieces per reel	2 mm x 2 mm, 0.50 mm nominal height MLP/DFN	40 to 95		
A3212ELHLT-T	3000 pieces per reel	3-pin surface mount SOT23W	-40 to 85		
A3212EUA-T	500 pieces per bulk bag	SIP-3 through hole		On	
A3212LLHLT-T	3000 pieces per reel	3-pin surface mount SOT23W	40 to 150		
A3212LUA-T	500 pieces per bulk bag	SIP-3 through hole	-40 to 150		

¹Contact Allegro for additional packaging and handling options.

²Variant is in production but has been determined to be NOT FOR NEW DESIGN. This classification indicates that sale of the variant is currently restricted to existing customer applications. The variant should not be purchased for new design applications because obsolescence in the near future is probable. Samples are no longer available. Status change: May 4, 2009.

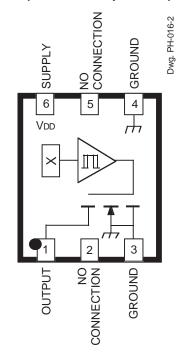


Absolute Maximum Ratings

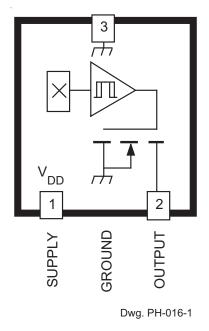
Characteristic	Symbol	Notes	Rating	Units
Supply Voltage	V_{DD}		5	V
Magnetic Flux Density	В		Unlimited	G
Output Off Voltage	V _{OUT}		5	V
Output Current	I _{OUT}		1	mA
On anating Amphicut Townsonstons	T _A	Range E	-40 to 85	°C
Operating Ambient Temperature		Range L	-40 to 150	°C
Maximum Junction Temperature	T _J (max)		165	°C
Storage Temperature	T _{stg}		-65 to 170	°C



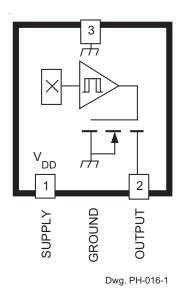
Package Suffix 'EH' Pinning (Leadless Chip Carrier)



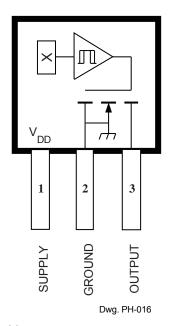
Package Suffix 'LH' Pinning (SOT23W)



Package Suffix 'EL' Pinning (Leadless Chip Carrier)



Package Suffix 'UA' Pinning (SIP)



Pinning is shown viewed from branded side.



ELECTRICAL CHARACTERISTICS over operating voltage and temperature range (unless otherwise specified).

Characteristic	Symbol	Test Conditions	Limits				
Characteristic			Min.	Typ.*	Max.	Units	
Supply Voltage Range	V _{DD}	Operating	2.5	2.75	3.5	V	
Output Leakage Current	I _{OFF}	V _{OUT} = 3.5 V, Output off	_	<1.0	1.0	μA	
Output On Voltage	V _{OUT}	I _{OUT} = 1 mA, V _{DD} = 2.75 V	_	100	300	mV	
Awake Time	t _{awake}		_	45	90	μs	
Period	t _{period}		_	45	90	ms	
Duty Cycle	d.c.		_	0.1	_	%	
Chopping Frequency	f _C		_	340	-	kHz	
	I _{DD(EN)}	Chip awake (enabled)	_	_	2.0	mA	
Supply Current	I _{DD(DIS)}	Chip asleep (disabled)	_	_	8.0	μA	
Supply Culterit	I _{DD(AVG)}	V _{DD} = 2.75 V	_	5.1	10	μA	
		V _{DD} = 3.5 V	_	6.7	10	μA	

^{*} Typical data is at $T_A = 25$ °C and $V_{DD} = 2.75$ V, and is for design information only.

A3211 MAGNETIC CHARACTERISTICS over operating voltage range (unless otherwise specified)

Characteristic	Symbol	Test Conditions	Limits			
Gilaracteristic Symb		rest Conditions		Тур.	Max.	Units
Over Temperature Range E: T _A = -40°C to 85°C						
Operate Points -	B _{OPS}	South pole to branded side; B > B _{OP} , V _{OUT} = High (Output Off)	_	37	55	G
	B _{OPN}	North pole to branded side; $B > B_{OP}$, $V_{OUT} = High$ (Output Off)	- 55	-4 0	_	G
Release Points	B _{RPS}	South pole to branded side; B < B _{RP} , V _{OUT} = Low (Output On)	10	31	-	G
Release Points	B _{RPN}	North pole to branded side; $B < B_{RP}$, $V_{OUT} = Low (Output On)$	_	-34	-10	G
Hysteresis	B _{HYS}	B _{OPx} - B _{RPx}	-	5.9		G

- NOTES: 1. Negative flux densities are defined as less than zero (algebraic convention), i.e., -50 G is less than +10 G.
 - 2. B_{OPx} = operate point (output turns off); B_{RPx} = release point (output turns on).
 - 3. Typical Data is at $T_A = +25^{\circ}$ C and $V_{DD} = 2.75$ V and is for design information only.
 - 4. 1 gauss (G) is exactly equal to 0.1 millitesla (mT).

A3212 MAGNETIC CHARACTERISTICS over operating voltage range (unless otherwise specified)

Characteristic	Cumbal	Took Conditions	Limits				
Characteristic Symbol		Test Conditions		Тур.	Max.	Units	
Over Temperature Range E: T _A = -40°C to 85°C							
Operate Points	B _{OPS}	South pole to branded side; $B > B_{OP}$, $V_{OUT} = Low (Output On)$	-	37	55	G	
Operate Points	B _{OPN}	North pole to branded side; $B > B_{OP}$, $V_{OUT} = Low (Output On)$	- 55	-4 0	-	G	
Pologgo Pointo	B _{RPS}	South pole to branded side; $B < B_{RP}$, $V_{OUT} = High (Output Off)$	10	31	_	G	
Release Points	B _{RPN}	North pole to branded side; $B < B_{RP}$, $V_{OUT} = High$ (Output Off)	-	-34	-10	G	
Hysteresis	B _{HYS}	B _{OPx} - B _{RPx}	_	5.9	_	G	
Over Temperature	Over Temperature Range L: T _A = -40°C to 150°C						
Operate Points	B _{OPS}	South pole to branded side; $B > B_{OP}$, $V_{OUT} = Low (Output On)$	-	37	65	G	
Operate Points	B _{OPN}	North pole to branded side; B > B _{OP} , V _{OUT} = Low (Output On)	-65	-40	_	G	
Release Points	B _{RPS}	South pole to branded side; $B < B_{RP}$, $V_{OUT} = High (Output Off)$	10	31	_	G	
	B _{RPN}	North pole to branded side; $B < B_{RP}$, $V_{OUT} = High$ (Output Off)	_	-34	-10	G	
Hysteresis	B _{HYS}	$ B_{OPx} - B_{RPx} $	_	5.9	_	G	

- NOTES: 1. Negative flux densities are defined as less than zero (algebraic convention), i.e., -50 G is less than +10 G.

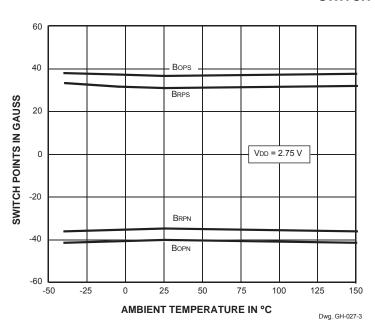
 - 2. B_{OPx} = operate point (output turns on); B_{RPx} = release point (output turns off). 3. Typical Data is at T_A = +25°C and V_{DD} = 2.75 V and is for design information only.
 - 4. 1 gauss (G) is exactly equal to 0.1 millitesla (mT).

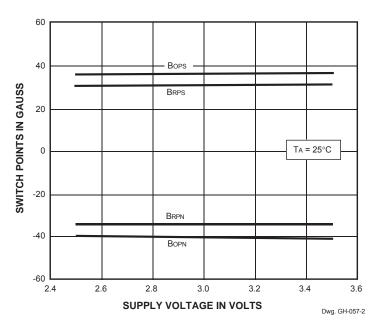


Allegro MicroSystems, Inc.

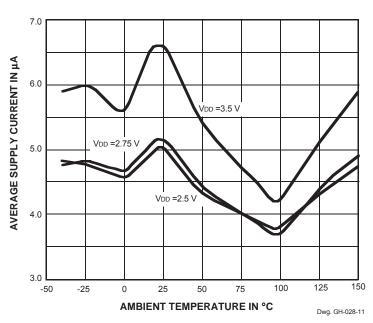
TYPICAL OPERATING CHARACTERISTICS

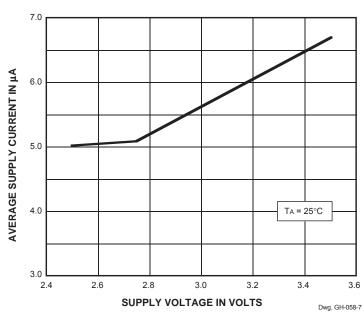
SWITCH POINTS





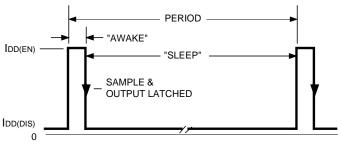
SUPPLY CURRENT



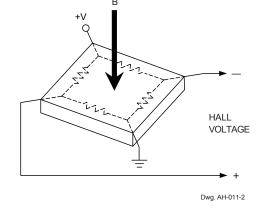


FUNCTIONAL DESCRIPTION

Low Average Power. Internal timing circuitry activates the sensor for 45 μ s and deactivates it for the remainder of the period (45 ms). A short "awake" time allows for stabilization prior to the sensor sampling and data latching on the falling edge of the timing pulse. The output during the "sleep" time is latched in the last sampled state. The supply current is not affected by the output state.

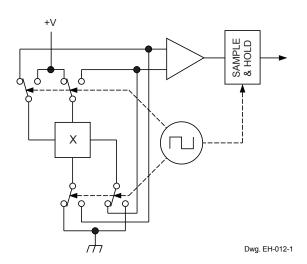


Dwg. WH-017-2



Chopper-Stabilized Technique. The Hall element can be considered as a resistor array similar to a Wheatstone bridge. A large portion of the offset is a result of the mismatching of these resistors. These devices use a proprietary dynamic offset cancellation technique, with an internal high-frequency clock to reduce the residual offset voltage of the Hall element that is normally caused by device overmolding, temperature dependencies, and thermal stress. The chopper-stabilizing technique cancels the mismatching of the resistor circuit by changing the direction of the current flowing through the Hall plate using CMOS switches and Hall voltage measurement taps, while maintaing the Hallvoltage signal that is induced by the external magnetic flux. The signal is then captured by a sample-and-hold circuit and further processed using low-offset bipolar circuitry. This technique produces devices that have an extremely stable quiescent Hall output voltage, are immune to thermal stress, and have precise recoverability after temperature cycling. A relatively high sampling frequency is used for faster signal processing capability can be processed.

More detailed descriptions of the circuit operation can be found in: Technical Paper STP 97-10, *Monolithic Magnetic Hall Sensor Using Dynamic Quadrature Offset Cancellation* and Technical Paper STP 99-1, *Chopper-Stabilized Amplifiers With A Track-and-Hold Signal Demodulator*.



A3211 and

A3212

FUNCTIONAL DESCRIPTION (cont'd)

Operation. The output of the A3212 switches low (turns on) when a magnetic field perpendicular to the Hall sensor exceeds the operate point B_{OPS} (or is less than B_{OPN}). After turn-on, the output is capable of sinking up to 1 mA and the output voltage is $V_{OUT(ON)}$. When the magnetic field is reduced below the release point B_{RPS} (or increased above B_{RPN}), the device output switches high (turns off). The difference in the magnetic operate and release points is the hysteresis (B_{hys}) of the device. This built-in hysteresis allows clean switching of the output even in the presence of external mechanical vibration and electrical noise. The A3211 functions in the same manner, except the output voltage is reversed from the A3212, as shown in the figures to the right.

As used here, negative flux densities are defined as less than zero (algebraic convention), i.e., -50 G is less than +10 G.

Applications. Allegro's pole-independent sensing technique allows for operation with either a north pole or south pole magnet orientation, enhancing the manufacturability of the device. The state-of-the-art technology provides the same output polarity for either pole face.

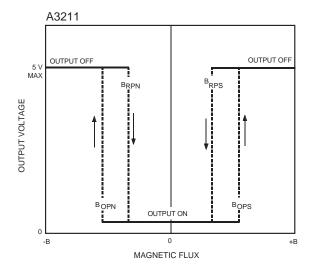
It is strongly recommended that an external bypass capacitor be connected (in close proximity to the Hall sensor) between the supply and ground of the device to reduce both external noise and noise generated by the chopper-stabilization technique. This is especially true due to the relatively high impedance of battery supplies.

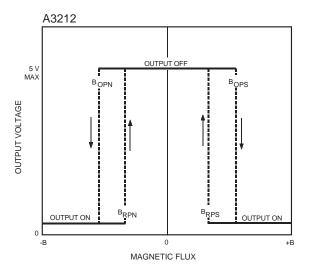
The simplest form of magnet that will operate these devices is a bar magnet with either pole near the branded surface of the device. Many other methods of operation are possible. Extensive applications information for Hall-effect sensors is available in:

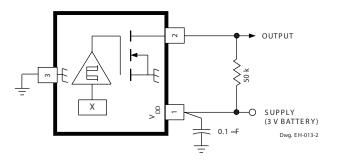
- Hall-Effect IC Applications Guide, Application Note 27701;
- Hall-Effect Devices: Soldering, Gluing, Potting, Encapsulating, and Lead Forming, Application Note 27703.1;
- Soldering of Through-Hole Hall-Sensor Dervices, Application Note 27703; and
- Soldering of Surface-Mount Hall-Sensor Devices, Application Note 27703.2.

All are provided at

www.allegromicro.com

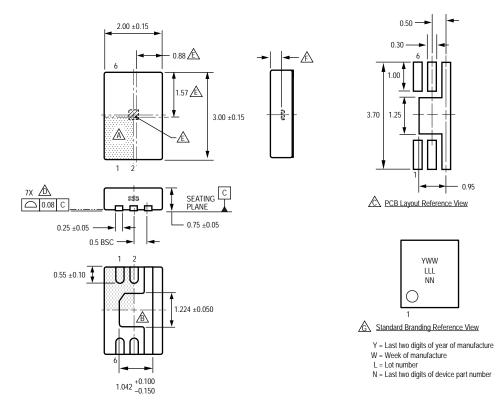








Package EH, 6-Contact MLP/DFN



For Reference Only, not for tooling use (reference DWG-2861; reference JEDEC MO-229WCED, Type 1)
Dimensions in millimeters

Exact case and lead configuration at supplier discretion within limits shown

A Terminal #1 mark area

Exposed thermal pad (reference only, terminal #1 identifier appearance at supplier discretion)

Reference land pattern layout;

All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances; when mounting on a multilayer PCB, thermal vias at the exposed thermal pad land can improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5)

Coplanarity includes exposed thermal pad and terminals

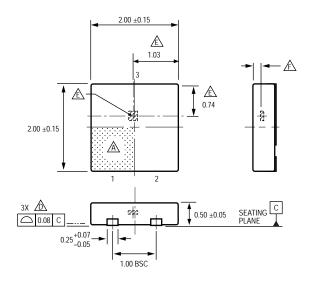
Hall Element (not to scale); U.S. customary dimensions controlling

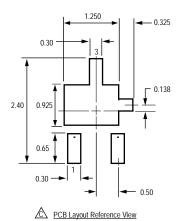
Active Area Depth, 0.32 mm NOM

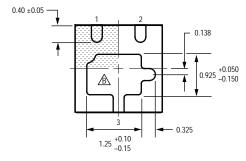
Branding scale and appearance at supplier discretion



Package EL, 3-Contact MLP/DFN









Standard Branding Reference View

Y = Last two digits of year of manufacture W = Week of manufacture

N = Last two digits of device part number

For Reference Only, not for tooling use (reference DWG-2865; reference JEDEC MO-229UCCD)

Dimensions in millimeters Exact case and lead configuration at supplier discretion within limits shown

A Terminal #1 mark area

Exposed thermal pad (reference only, terminal #1 identifier appearance at supplier discretion)

Reference land pattern layout (reference IPC7351); All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances; when mounting on a multilayer PCB, thermal vias at the exposed thermal pad land can improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5) Coplanarity includes exposed thermal pad and terminals

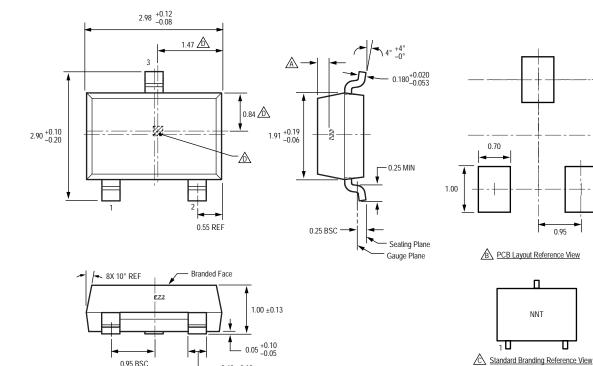
All Element (not to scale)

Active Area Depth, 0.18 mm NOM

Branding scale and appearance at supplier discretion

2.40

Package LH, 3-Pin; (SOT-23W)



0.40 ±0.10

For Reference Only; not for tooling use (reference dwg. 802840)

0.95 BSC

Dimensions in millimeters
Dimensions exclusive of mold flash, gate burrs, and dambar protrusions Exact case and lead configuration at supplier discretion within limits shown

Active Area Depth, 0.28 mm REF

Reference land pattern layout
All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances

Branding scale and appearance at supplier discretion

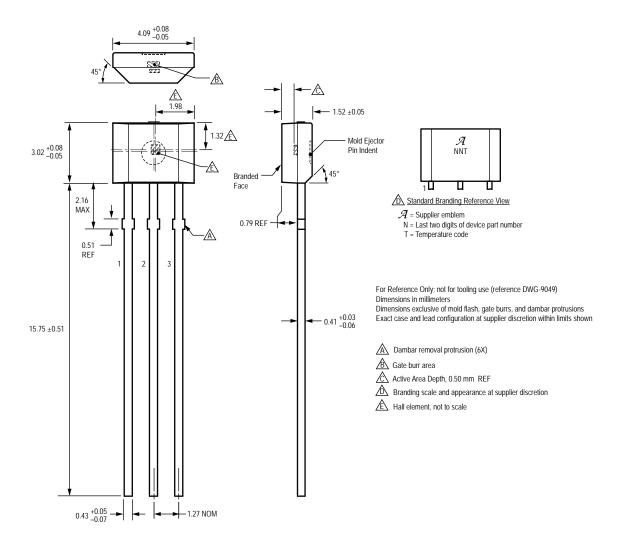
hall element, not to scale



N = Last two digits of device part number

T = Temperature code

Package UA, 3-Pin SIP



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The products described herein are manufactured under one or more of the following U.S. patents: 5,045,920; 5,264,783; 5,442,283; 5,389,889; 5,581,179; 5,517,112; 5,619,137; 5,621,319; 5,650,719; 5,686,894; 5,694,038; 5,729,130; 5,917,320; and other patents pending.

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